



N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	Rds(on) Max	I _{D MAX} Ta = +25°C
	$29m\Omega$ @ V _{GS} = 4.5V	5.6A
12V	$34m\Omega$ @ V _{GS} = 2.5V	5.1A
120	44mΩ @ V _{GS} = 1.8V	4.5A
	$65m\Omega @ V_{GS} = 1.5V$	3.7A

Description

This MOSFET has been designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

Applications

- Load switches
- · Power-management functions
- Portable power adaptors

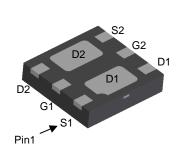
Features

- Low On-Resistance
- Low Input Capacitance
- Low Profile, 0.6mm Max Height
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

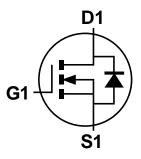
Mechanical Data

- Package: U-DFN2020-6
- Package Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @4
- Terminals Connections: See Diagram Below
- Weight: 0.0065 grams (Approximate)

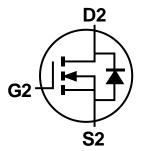
U-DFN2020-6 (Type B)



Bottom View



Q1 N-CHANNEL MOSFET



Q2 N-CHANNEL MOSFET

Internal Schematic

Ordering Information (Note 4)

Part Number	Packago	Packing		
Fait Nullibei	Package	Qty.	Carrier	
DMN1029UFDB-7	U-DFN2020-6 (Type B)	3000	Tape & Reel	
DMN1029UFDB-13	U-DFN2020-6 (Type B)	10000	Tape & Reel	

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



Marking Information

Site 1



D5 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: K = 2023)M = Month (ex: 9 = September)

Date Code Key

Ye	ear	2015		2023	2024	2025	2026	2027	2028	2029	2030	2031	2032
Co	ode	С		K	L	M	Ν	Р	R	S	Т	U	V
										_		_	
Мо	onth	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

Site 2



D5 = Product Type Marking Code YWX = Date Code Marking Y = Year (ex: 3 = 2023)

W = Week (ex: a = week 27; z represents week 52 and 53) X = Internal Code (ex: U = Monday)

Date Code Kev

Year	2015	 2023	2024	2025	2026	2027	2028	2029	2030	2031	2032
Code	5	 3	4	5	6	7	8	9	0	1	2

Week	1-26	27-52	53
Code	A-Z	a-z	Z

Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat
Code	Т	U	V	W	Χ	Υ	Z



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	VDSS	12	V		
Gate-Source Voltage			V_{GSS}	±8	V
Continuous Drain Current (Note EV)	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	lo	5.6 4.4	А
Continuous Drain Current (Note 5) V _{GS} = 4.5V	t < 5s	$T_A = +25$ °C $T_A = +70$ °C	lο	7.2 5.8	А
Maximum Continuous Body Diode Forward Curre	ent (Note 5)		Is	1	Α
Pulsed Drain Current (10µs pulse, Duty Cycle =	1%)		Ірм	20	Α
Avalanche Current (L = 0.1mH)			las	15	A
Avalanche Energy (L = 0.1mH)	•		Eas	12	mJ

Thermal Characteristics

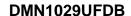
Characteristic		Symbol	Value	Unit	
Total Dawar Dissipation (Note 5)	Steady State	D-	1.4	W	
Total Power Dissipation (Note 5)	t < 5s	P _D	2.2	VV	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Б	91		
Thermal Resistance, Junction to Ambient (Note 5)	t < 5s	$R_{\theta JA}$	55	°C/W	
Thermal Resistance, Junction to Case	R _θ JC	20			
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

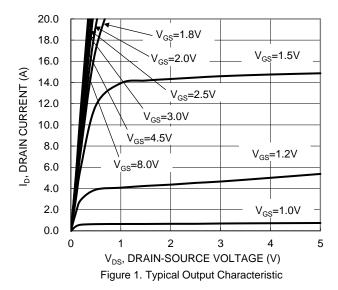
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage	BV _{DSS}	12	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	IDSS	_	_	1.0	μΑ	V _{DS} = 12V, V _{GS} = 0V	
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 8V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage	Vgs(TH)	0.4	_	1	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
			17	29		$V_{GS} = 4.5V, I_D = 5A$	
Statia Drain Sauras On Benjatanas	D	_	20	34	~ 0	$V_{GS} = 2.5V, I_{D} = 4.6A$	
Static Drain-Source On-Resistance	RDS(ON)	_	24	44	mΩ	$V_{GS} = 1.8V, I_{D} = 4.1A$	
		_	30	65		V _G S = 1.5V, I _D = 2A	
Diode Forward Voltage	VsD	_	0.6	1.2	V	V _G S = 0V, I _S = 1A	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	Ciss		914	_	pF	.,	
Output Capacitance	Coss		132	_	pF	V _{DS} = 6V, V _{GS} = 0V, f = 1.0MHz	
Reverse Transfer Capacitance	Crss	_	119	_	pF	1 = 1.0WH 12	
Gate Resistance	Rg	_	1.26	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)		_	10.5	_	nC		
Total Gate Charge (VGS = 8V)	Qg	_	19.6	_	nC	\/ O\/ I O.5A	
Gate-Source Charge	Qgs	_	1.2	_	nC	$V_{DS} = 6V, I_{D} = 6.5A$	
Gate-Drain Charge	Q _{gd}	_	1.6	_	nC		
Turn-On Delay Time	tD(ON)		5.0	_	ns		
Turn-On Rise Time	tR		10.5	_	ns	$V_{DD} = 6V, V_{GS} = 4.5V,$	
Turn-Off Delay Time	tD(OFF)		16.6	_	ns	$R_L = 1.2\Omega$, $R_G = 1\Omega$	
Turn-Off Fall Time	tF	_	4.1	_	ns	7	

Notes: 5. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.

Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.







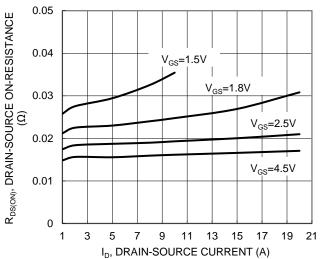


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

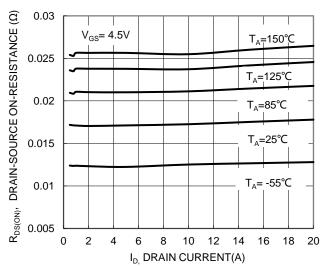
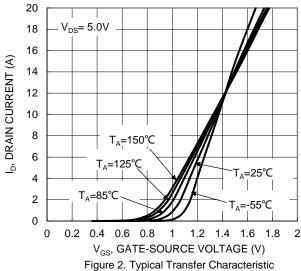
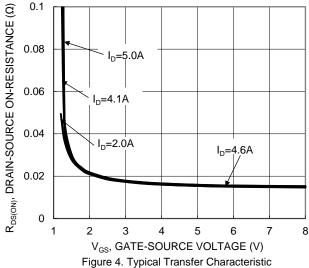


Figure 5. Typical On-Resistance vs. Drain Current and Temperature



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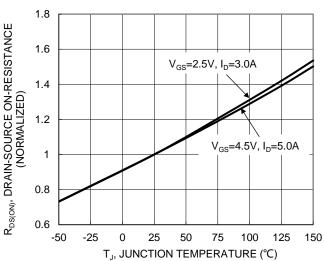


Figure 6. On-Resistance Variation with Temperature

DMN1029UFDB



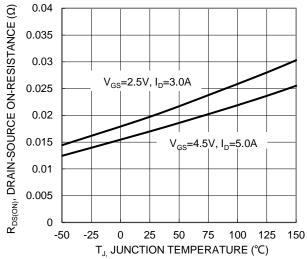


Figure 7. On-Resistance Variation with Temperature

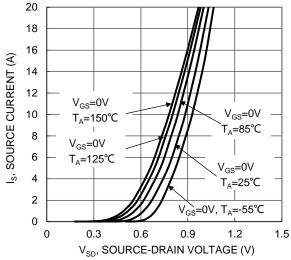
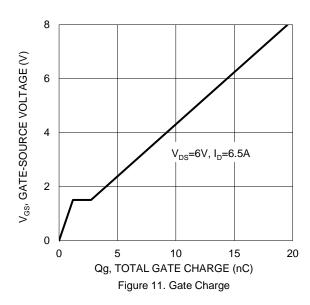


Figure 9. Diode Forward Voltage vs. Current



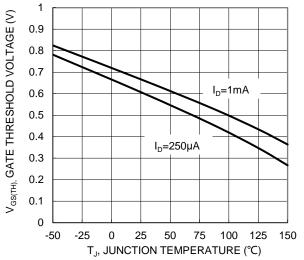


Figure 8. Gate Threshold Variation vs. Junction Temperature

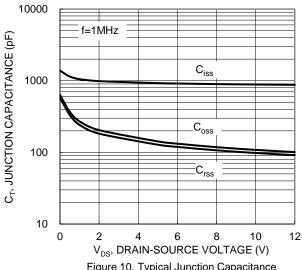
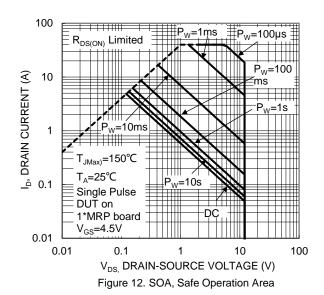


Figure 10. Typical Junction Capacitance





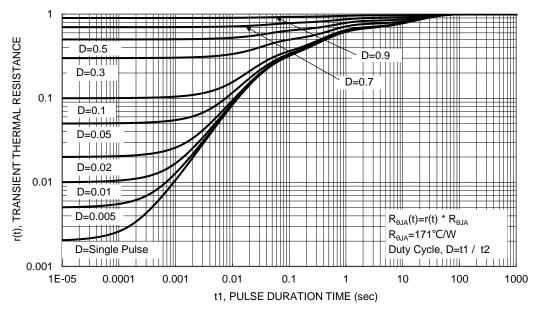


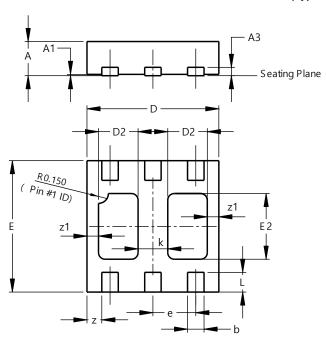
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type B)

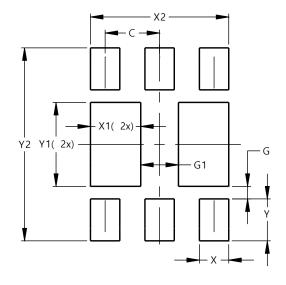


	U-DFN2020-6 Type B							
Dim	71							
Α	0.545	0.605	0.575					
A1	0.00	0.05	0.02					
A3	-	-	0.13					
b	0.20	0.30	0.25					
D	1.95	2.075	2.00					
D2	0.50	0.70	0.60					
е	-	-	0.65					
Е	1.95	2.075	2.00					
E2	0.90	1.10	1.00					
k	-	-	0.45					
L	0.25	0.35	0.30					
Z	-	-	0.225					
z1	-	-	0.175					
All	Dimens	ions in	mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type B)



Dimensions	Value (in mm)		
С	0.650		
G	0.150		
G1	0.450		
X	0.350		
X1	0.600		
X2	1.650		
Y	0.500		
Y1	1.000		
Y2	2.300		



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